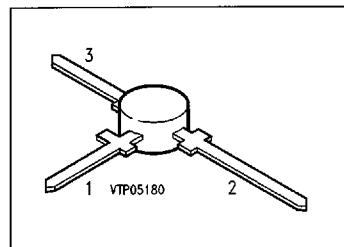


NPN Silicon RF Transistor

BFR 96S

- For low-noise, low-distortion broadband amplifiers in antenna and telecommunications systems up to 2 GHz at collector currents from 10 mA to 70 mA.



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration			Package ¹⁾
			1	2	3	
BFR 96S	BFR 96S	Q68000-A5689	E	C	B	T-plast

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CEO}	15	V
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	3	
Collector current	I_C	100	mA
Total power dissipation, $T_S \leq 87^\circ\text{C}$ ³⁾	P_{tot}	700	mW
Junction temperature	T_J	150	$^\circ\text{C}$
Ambient temperature range	T_A	- 65 ... + 150	
Storage temperature range	T_{stg}	- 65 ... + 150	
Thermal Resistance			
Junction - ambient ²⁾	$R_{th JA}$	≤ 170	K/W
Junction - soldering point ³⁾	$R_{th JS}$	≤ 90	

1) For detailed dimensions see chapter Package Outlines.

2) Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.

3) T_S is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(\text{BR})\text{CE}0}$	15	—	—	V
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	I_{CB0}	—	—	100	nA
Emitter-base cutoff current $V_{EB} = 3 \text{ V}, I_C = 0$	I_{EB0}	—	—	100	μA
DC current gain $I_C = 70 \text{ mA}, V_{CE} = 10 \text{ V}$	h_{FE}	25	75	—	—
Collector-emitter saturation voltage $I_C = 75 \text{ mA}, I_B = 7.5 \text{ mA}$	$V_{CE\text{sat}}$	—	0.13	0.5	V

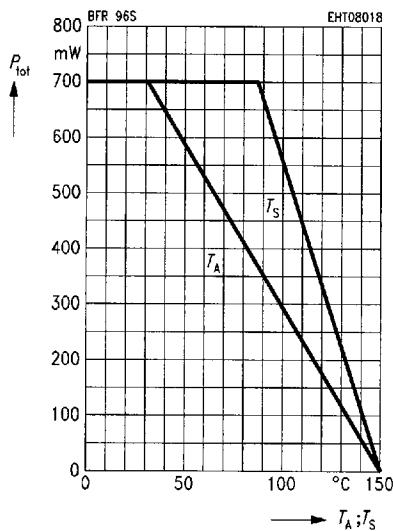
Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

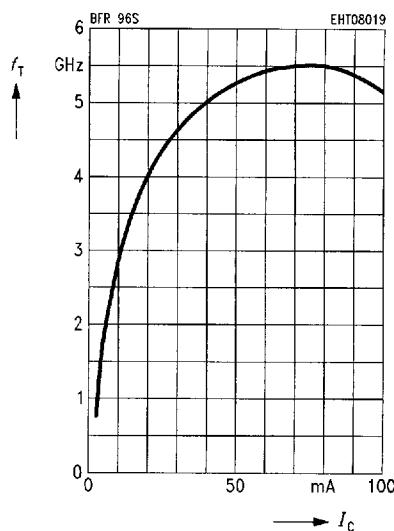
AC Characteristics

Transition frequency $I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V}, f = 200 \text{ MHz}$ $I_C = 70 \text{ mA}, V_{CE} = 10 \text{ V}, f = 200 \text{ MHz}$	f_T	— —	5.3 5.5	— —	GHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, V_{BE} = V_{BE} = 0, f = 1 \text{ MHz}$	C_{cb}	—	0.95	—	pF
Collector-emitter capacitance $V_{CE} = 10 \text{ V}, V_{BE} = V_{BE} = 0, f = 1 \text{ MHz}$	C_{ce}	—	0.3	—	
Input capacitance $V_{EB} = 0.5 \text{ V}, I_C = i_c = 0, f = 1 \text{ MHz}$	C_{ib}	—	5	—	
Output capacitance $V_{CE} = 10 \text{ V}, V_{BE} = V_{BE} = 0, f = 1 \text{ MHz}$	C_{obs}	—	1.25	—	
Noise figure $I_C = 5 \text{ mA}, V_{CE} = 10 \text{ V}, f = 10 \text{ MHz}, Z_S = 50 \Omega$ $I_C = 70 \text{ mA}, V_{CE} = 10 \text{ V}, f = 800 \text{ MHz}, Z_S = Z_{\text{sopt}}$	F	— —	0.9 2.9	— —	dB
Power gain $I_C = 70 \text{ mA}, V_{CE} = 10 \text{ V}, f = 800 \text{ MHz},$ $Z_S = Z_{\text{sopt}}, Z_L = Z_{\text{lopt}}$	G_{pe}	—	11.5	—	
Transducer gain $I_C = 70 \text{ mA}, V_{CE} = 10 \text{ V}, f = 500 \text{ MHz}, Z_0 = 50 \Omega$	$ S_{21e} ^2$	—	14.8	—	
Linear output voltage two-tone intermodulation test $I_C = 70 \text{ mA}, V_{CE} = 10 \text{ V}, d_{IM} = 60 \text{ dB}$ $f_1 = 806 \text{ MHz}, f_2 = 810 \text{ MHz}, Z_S = Z_L = 50 \Omega$	$V_{o1} = V_{o2}$	—	500	—	mV
Third order intercept point $I_C = 70 \text{ mA}, V_{CE} = 10 \text{ V}, f = 800 \text{ MHz}$	IP_3	—	37	—	dBm

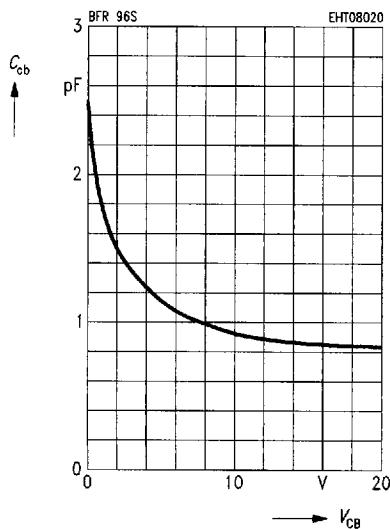
Total power dissipation $P_{\text{tot}} = f(T_A^*, T_S)$
 * Package mounted on alumina



Transition frequency $f_T = f(I_C)$
 $V_{CE} = 10 \text{ V}$, $f = 200 \text{ MHz}$



Collector-base capacitance $C_{cb} = f(V_{CB})$
 $V_{BE} = v_{be} = 0$, $f = 1 \text{ MHz}$



Common Emitter Noise Parameters

<i>f</i>	<i>F</i> _{min}	<i>G_p</i> (<i>F</i> _{min})	Γ_{opt}		<i>R_N</i>	<i>N</i>	<i>F</i> _{50Ω}	<i>G_p</i> (<i>F</i> _{50Ω})
GHz	dB	dB	MAG	ANG	Ω	-	dB	dB

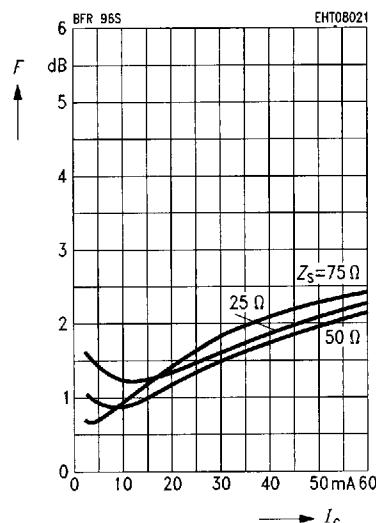
I_c = 10 mA, *V_{CE}* = 10 V, *Z₀* = 50 Ω

0.01	-	-	-	-	-	-	1.05	-
0.8	2.2	-	0.41	-170.3	6.6	0.31	2.8	-

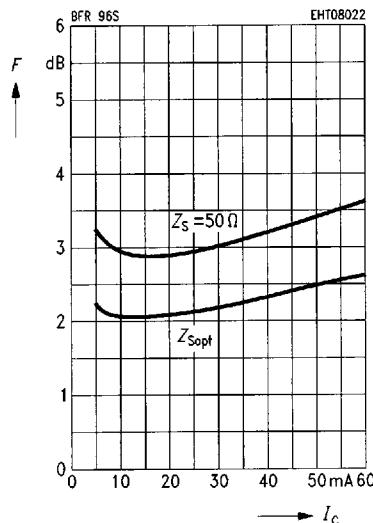
I_c = 70 mA, *V_{CE}* = 10 V, *Z₀* = 50 Ω

0.01	-	-	-	-	-	-	2.3	-
0.8	2.9	-	0.43	-163	10	0.45	2.9	-

Noise figure $F = f(I_c)$
V_{CE} = 10 V, *f* = 10 MHz



Noise figure $F = f(I_c)$
V_{CE} = 10 V, *f* = 800 MHz

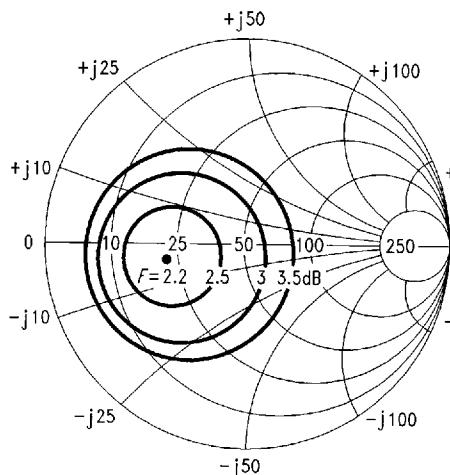


Circles of constant noise figure $F = f(Z_s)$

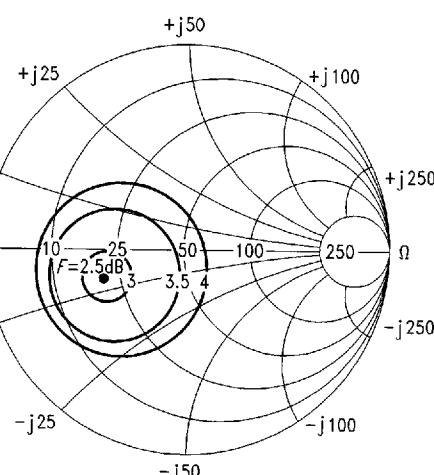
$I_C = 10 \text{ mA}$, $V_{CE} = 10 \text{ V}$, $f = 800 \text{ MHz}$,
 $R_N = 6.6 \Omega$, $N = 0.31$, $\Gamma_{\text{opt}} = 0.41 < -170^\circ$

Circles of constant noise figure $F = f(Z_s)$

$I_C = 70 \text{ mA}$, $V_{CE} = 10 \text{ V}$, $f = 800 \text{ MHz}$,
 $R_N = 10 \Omega$, $F_{\min} = 2.9 \text{ dB}$, $\Gamma_{\text{opt}} = 0.43 < -163^\circ$



EHT08023



EHT08024

■ 8235605 0067342 495 ■

Common Emitter S Parameters

<i>f</i> GHz	<i>S</i> ₁₁		<i>S</i> ₂₁		<i>S</i> ₁₂		<i>S</i> ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
<i>I</i> _C = 50 mA, <i>V</i> _{CE} = 5 V, <i>Z</i> ₀ = 50 Ω								
0.1	0.42	- 143.2	26.24	104.5	0.022	64.4	0.31	- 63.9
0.2	0.40	- 167.1	13.22	91.6	0.040	69.7	0.17	- 67.8
0.3	0.41	- 178.2	8.81	84.0	0.058	71.1	0.12	- 68.9
0.4	0.41	173.9	6.60	78.5	0.076	70.5	0.10	- 70.4
0.5	0.42	167.2	5.30	73.4	0.094	69.0	0.09	- 72.9
0.6	0.43	161.5	4.44	68.6	0.112	67.1	0.08	- 77.8
0.7	0.44	155.8	3.82	64.0	0.129	65.2	0.07	- 82.7
0.8	0.44	151.1	3.34	59.8	0.147	63.7	0.07	- 84.6
0.9	0.44	147.0	2.99	55.6	0.166	61.0	0.07	- 93.6
1.0	0.45	142.2	2.71	51.5	0.182	58.5	0.06	- 104.2
1.1	0.46	138.1	2.49	47.5	0.199	56.0	0.06	- 115.7
1.2	0.47	133.9	2.29	43.6	0.215	53.6	0.06	- 127.8
1.3	0.49	129.6	2.14	39.7	0.231	51.2	0.06	- 140.0
1.4	0.49	125.5	2.00	35.9	0.246	48.7	0.07	- 151.7
1.5	0.51	121.6	1.89	32.1	0.262	46.2	0.07	- 160.1
1.6	0.51	118.0	1.79	28.3	0.276	43.6	0.08	- 167.6
1.7	0.53	114.6	1.69	24.7	0.290	40.9	0.09	- 175.5
1.8	0.54	111.4	1.61	21.3	0.303	38.4	0.10	176.9
1.9	0.55	108.6	1.54	17.9	0.316	36.0	0.11	170.1
2.0	0.57	105.4	1.47	14.6	0.328	33.6	0.12	163.6

*I*_C = 10 mA, *V*_{CE} = 10 V, *Z*₀ = 50 Ω

0.1	0.63	- 89.9	18.56	124.5	0.033	54.7	0.66	- 33.9
0.2	0.51	- 131.0	10.78	102.9	0.046	50.1	0.45	- 38.3
0.3	0.48	- 153.7	7.43	91.4	0.056	52.9	0.38	- 37.4
0.4	0.47	- 166.9	5.64	83.6	0.066	55.4	0.34	- 36.8
0.5	0.47	- 177.9	4.55	77.1	0.078	57.1	0.32	- 37.3
0.6	0.48	173.4	3.82	71.2	0.090	58.1	0.31	- 38.8
0.7	0.48	165.9	3.29	65.9	0.101	58.7	0.30	- 40.7
0.8	0.48	159.6	2.89	61.0	0.114	59.4	0.30	- 42.6
0.9	0.49	154.1	2.59	56.3	0.128	58.9	0.29	- 45.9
1.0	0.50	148.3	2.35	51.7	0.141	58.0	0.28	- 49.4
1.1	0.51	143.2	2.16	47.4	0.155	57.0	0.28	- 53.1
1.2	0.52	138.3	1.99	43.2	0.168	56.0	0.27	- 56.9
1.3	0.53	133.2	1.86	38.9	0.182	54.8	0.26	- 61.0
1.4	0.54	128.8	1.74	34.8	0.196	53.5	0.25	- 65.4
1.5	0.55	124.6	1.64	30.9	0.210	52.0	0.25	- 70.2
1.6	0.56	120.4	1.55	26.9	0.224	50.3	0.25	- 75.7
1.7	0.57	116.7	1.47	23.1	0.238	48.5	0.24	- 81.8
1.8	0.58	113.1	1.40	19.6	0.252	46.8	0.24	- 87.5
1.9	0.59	109.7	1.33	16.2	0.266	45.0	0.23	- 94.1
2.0	0.61	106.2	1.28	12.7	0.280	43.2	0.23	- 101.3

Common Emitter S Parameters (continued)

<i>f</i>	<i>S</i> ₁₁		<i>S</i> ₂₁		<i>S</i> ₁₂		<i>S</i> ₂₂	
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG

I_c = 30 mA, *V_{CE}* = 10 V, *Z₀* = 50 Ω

0.1	0.44	-120.4	25.96	110.4	0.024	58.3	0.43	- 48.5
0.2	0.40	-154.1	13.48	94.9	0.039	64.6	0.27	- 48.0
0.3	0.39	-169.6	9.04	86.3	0.054	67.4	0.21	- 45.3
0.4	0.39	-179.2	6.79	80.3	0.070	67.6	0.19	- 43.8
0.5	0.39	172.5	5.45	74.9	0.086	67.1	0.17	- 43.7
0.6	0.40	165.9	4.57	69.9	0.101	65.8	0.16	- 45.3
0.7	0.41	159.7	3.93	65.2	0.117	64.6	0.15	- 46.9
0.8	0.41	154.4	3.44	60.9	0.133	63.5	0.15	- 48.1
0.9	0.42	150.3	3.08	56.7	0.150	61.4	0.15	- 52.2
1.0	0.43	144.7	2.79	52.5	0.165	59.3	0.14	- 56.7
1.1	0.44	140.3	2.56	48.5	0.180	57.2	0.13	- 61.0
1.2	0.45	136.1	2.36	44.6	0.195	55.1	0.12	- 66.0
1.3	0.46	131.3	2.20	40.6	0.209	53.0	0.11	- 71.1
1.4	0.47	127.3	2.06	36.7	0.224	50.8	0.10	- 77.2
1.5	0.48	123.6	1.94	33.0	0.238	48.6	0.10	- 84.1
1.6	0.49	120.0	1.84	29.1	0.253	46.3	0.10	- 92.9
1.7	0.51	116.5	1.74	25.5	0.266	43.9	0.09	- 103.1
1.8	0.52	113.1	1.66	22.0	0.279	41.6	0.09	- 112.9
1.9	0.53	110.2	1.58	18.7	0.291	39.4	0.09	- 124.1
2.0	0.55	106.9	1.51	15.3	0.304	37.2	0.09	- 136.5

I_c = 50 mA, *V_{CE}* = 10 V, *Z₀* = 50 Ω

0.1	0.42	-130.9	27.43	106.3	0.022	62.0	0.35	- 52.7
0.2	0.37	-161.1	13.90	92.6	0.038	68.5	0.21	- 50.4
0.3	0.37	-173.9	9.28	84.8	0.055	70.4	0.17	- 47.3
0.4	0.37	178.1	6.95	79.2	0.072	70.1	0.15	- 45.8
0.5	0.38	170.2	5.58	74.1	0.089	68.8	0.14	- 46.0
0.6	0.39	164.4	4.67	69.3	0.105	67.1	0.13	- 48.0
0.7	0.40	158.5	4.02	64.8	0.121	65.5	0.12	- 49.6
0.8	0.40	153.4	3.52	60.6	0.138	64.0	0.12	- 50.7
0.9	0.40	149.3	3.15	56.4	0.156	61.6	0.11	- 55.8
1.0	0.42	144.4	2.86	52.3	0.171	59.3	0.11	- 61.0
1.1	0.43	140.1	2.61	48.3	0.186	56.9	0.10	- 66.2
1.2	0.44	135.7	2.41	44.5	0.202	54.7	0.09	- 72.4
1.3	0.45	131.2	2.25	40.6	0.216	52.4	0.08	- 79.1
1.4	0.46	127.2	2.11	36.7	0.231	50.0	0.07	- 87.3
1.5	0.47	123.3	1.98	33.0	0.246	47.7	0.07	- 96.1
1.6	0.48	119.7	1.87	29.2	0.260	45.2	0.07	- 107.4
1.7	0.50	116.2	1.78	25.6	0.274	42.8	0.07	- 120.3
1.8	0.51	113.1	1.69	22.2	0.286	40.4	0.07	- 132.8
1.9	0.52	110.0	1.61	18.8	0.299	38.1	0.07	- 145.6
2.0	0.54	106.9	1.54	15.4	0.311	35.9	0.08	- 158.7

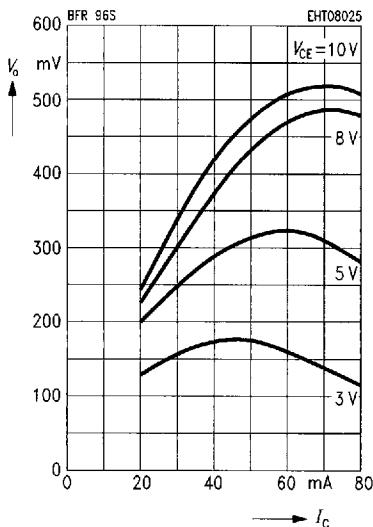
Common Emitter S Parameters (continued)

<i>f</i>	<i>S</i> ₁₁		<i>S</i> ₂₁		<i>S</i> ₁₂		<i>S</i> ₂₂	
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
<i>I</i> _C = 70 mA, <i>V</i> _{CE} = 10 V, <i>Z</i> ₀ = 50 Ω								
0.1	0.40	- 138.5	27.66	103.9	0.021	63.4	0.32	- 53.6
0.2	0.37	- 164.1	13.87	91.3	0.038	70.6	0.19	- 50.1
0.3	0.36	- 176.2	9.22	83.9	0.055	71.5	0.15	- 46.9
0.4	0.37	176.1	6.91	78.6	0.073	70.9	0.13	- 45.6
0.5	0.38	169.2	5.54	73.5	0.089	69.5	0.12	- 45.8
0.6	0.39	163.2	4.64	68.8	0.107	67.7	0.11	- 48.0
0.7	0.40	157.6	3.99	64.3	0.122	65.8	0.11	- 50.0
0.8	0.40	152.9	3.49	60.2	0.140	64.3	0.10	- 51.2
0.9	0.41	149.0	3.12	56.0	0.157	61.8	0.10	- 56.8
1.0	0.42	144.0	2.83	51.9	0.173	59.4	0.09	- 62.5
1.1	0.43	139.8	2.59	48.1	0.188	57.0	0.08	- 68.5
1.2	0.44	135.7	2.39	44.2	0.203	54.7	0.08	- 75.7
1.3	0.45	130.9	2.23	40.3	0.218	52.4	0.07	- 83.7
1.4	0.46	126.9	2.09	36.5	0.233	50.1	0.06	- 93.4
1.5	0.48	123.4	1.96	32.7	0.248	47.7	0.06	- 103.5
1.6	0.49	119.8	1.86	29.0	0.262	45.2	0.06	- 116.6
1.7	0.50	116.3	1.76	25.4	0.275	42.7	0.06	- 130.7
1.8	0.51	113.0	1.67	22.0	0.288	40.3	0.07	- 144.0
1.9	0.53	110.1	1.60	18.6	0.300	38.0	0.07	- 157.3
2.0	0.55	107.0	1.53	15.3	0.312	35.8	0.08	- 169.5

Common Emitter Large Signal Parameters

Linear output voltage $V_o = f(I_c)$

$d_{IM} = 60 \text{ dB}$, $f_1 = 806 \text{ MHz}$,
 $f_2 = 810 \text{ MHz}$, $Z_S = Z_L = 50 \Omega$



Note:

The transistor is driven by 2 adjacent signals f_1, f_2 with equal output power levels P_o for each carrier.

The distance d_{IM} between P_o and the third order intermodulation products P_{IM} ($2f_1 - f_2$ or $2f_2 - f_1$) is:

$$d_{IM} = P_o - P_{IM}$$

where $P_o = 10 \log (V_o^2 / (50 \Omega \cdot 1 \text{ mW}))$ (dBm)

and $V_o = \text{linear output voltage of each carrier}$.

The 3rd order intercept point IP_3 will be found by extrapolation to the point where P_{IM} would be identical to P_o :

$$IP_3 \text{ (output)} = P_o + d_{IM}/2.$$

Linear output voltages for other d_{IM} (e.g. 50 dB) can be calculated thereby.